High-Speed USB 2.0 (480 Mbps) DPDT Switches

The NLAS7242 is a DPDT switch optimized for high–speed USB 2.0 applications within portable systems. It features ultra–low on capacitance, $C_{\rm ON}$ = 7.5 pF (typ), and a bandwidth above 950 MHz. It is optimized for applications that use a single USB interface connector to route multiple signal types. The $C_{\rm ON}$ and $R_{\rm ON}$ of both channels are suitably low to allow the NLAS7242 to pass any speed USB data or audio signals going to a moderately resistive terminal such as an external headset. The device is offered in a UQFN10 1.4 mm x 1.8 mm package.

Features

- Optimized Flow-Through Pinout
- R_{ON} : 5.0 Ω Typ @ V_{CC} = 4.2 V
- C_{ON} : 7.5 pF Typ @ V_{CC} = 3.3 V
- V_{CC} Range: 1.65 V to 4.5 V
- Typical Bandwidth: 950 MHz
- 1.4 mm x 1.8 mm x 0.50 mm UQFN10
- OVT on Common Signal Pins D+/D- up to 5.25 V
- 8 kV HBM ESD Protection on All Pins
- This is a Pb-Free Device

Typical Applications

- High Speed USB 2.0 Data
- Mobile Phones
- Portable Devices

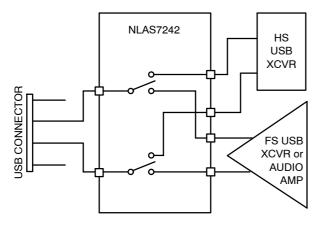


Figure 1. Application Diagram



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MARKING DIAGRAM



UQFN10 CASE 488AT



AD = Device Code

M = Date Code

■ Pb-Free Device

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NLAS7242MUTBG	UQFN0 (Pb-Free)	3000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

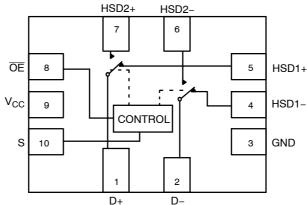


Figure 2. Pin Connections and Logic Diagram (Top View)

Table 1. PIN DESCRIPTION

Pin	Function
S	Control Input
ŌĒ	Output Enable
HSD1+, HSD1-, HSD2+, HSD2-, D+, D-	Data Ports

Table 2. TRUTH TABLE

ŌĒ	S	HSD1+, HSD1-	HSD2+, HSD2-
1	X	OFF	OFF
0	0	ON	OFF
0	1	OFF	ON

MAXIMUM RATINGS

Symbol	Pins	Parameter	Value	Unit
V _{CC}	V _{CC}	Positive DC Supply Voltage	-0.5 to +5.5	V
V _{IS}	HSDn+, HSDn-	Analog Signal Voltage	-0.5 to V_{CC} + 0.3	V
	D+, D-	1	-0.5 to +5.25	
V _{IN}	S, OE	Control Input Voltage, Output Enable Voltage	-0.5 to +5.5	V
I _{CC}	V _{CC}	Positive DC Supply Current	50	mA
T _S		Storage Temperature	-65 to +150	°C
I _{IS_CON}	HSDn+, HSDn-, D+, D-	Analog Signal Continuous Current-Closed Switch	±300	mA
I _{IS_PK}	HSDn+, HSDn-, D+, D-	Analog Signal Continuous Current 10% Duty Cycle	±500	mA
I _{IN}	S, OE	Control Input Current, Output Enable Current	±20	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Pins	Parameter	Min	Max	Unit
V_{CC}		Positive DC Supply Voltage	1.65	4.5	V
V _{IS}	HSDn+, HSDn-	Analog Signal Voltage	GND	V _{CC}	V
	D+, D-		GND	4.5	
V _{IN}	S, OE	Control Input Voltage, Output Enable Voltage	GND	V _{CC}	V
T _A		Operating Temperature	-40	+85	°C

Minimum and maximum values are guaranteed through test or design across the Recommended Operating Conditions, where applicable. Typical values are listed for guidance only and are based on the particular conditions listed for section, where applicable. These conditions are valid for all values found in the characteristics tables unless otherwise specified in the test conditions.

ESD PROTECTION

Symbol	Parameter	Value	Unit
ESD	Human Body Model - All Pins	8.0	kV

DC ELECTRICAL CHARACTERISTICS

CONTROL INPUT, OUTPUT ENABLE VOLTAGE (Typical: T = 25°C)

					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
V _{IH}	S, ŌE	Control Input, Output Enable HIGH Voltage (See Figure 11)		2.7 3.3 4.2	1.25 1.3 1.4	-	-	V
V _{IL}	S, OE	Control Input, Output Enable LOW Voltage (See Figure 11)		2.7 3.3 4.2	-	-	0.35 0.4 0.5	V
I _{IN}	S, OE	Current Input, Output Enable Leakage Current	$0 \le V_{IS} \le V_{CC}$	1.65 – 4.5	-	-	±1.0	μΑ

SUPPLY CURRENT AND LEAKAGE (Typical: T = 25°C, V_{CC} = 3.3 V)

					-4	-40°C to +85°C		
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
I _{CC}	V _{CC}	Quiescent Supply Current	$ 0 \le V_{IS} \le V_{CC}; \ I_D = 0 \ A $ $ 0 \le V_{IS} \le V_{CC} - 0.5 \ V $	1.65 – 3.6 3.6 – 4.5	- -	- -	1.0 1.0	μΑ
I _{OZ}		OFF State Leakage	$0 \le V_{IS} \le V_{CC}$	1.65 – 4.5	_	±0.1	±1.0	μΑ
l _{OFF}	D+, D-	Power OFF Leakage Current	$0 \le V_{IS} \le V_{CC}$	0	-	-	±1.0	μΑ

LIMITED V_{IS} **SWING ON RESISTANCE** (Typical: T = 25°C)

					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
R _{ON}		On–Resistance (Note 1)	I _{ON} = 8 mA V _{IS} = 0 V to 0.4 V	2.7 3.3 4.2	-	6.0 5.5 5.0	8.6 7.6 7.0	Ω
R _{FLAT}		On–Resistance Flatness (Notes 1 and 2)	I _{ON} = 8 mA V _{IS} = 0 V to 0.4 V	2.7 3.3 4.2	-	0.55 0.30 0.20	-	Ω
ΔR _{ON}		On–Resistance Matching (Notes 1 and 3)	I _{ON} = 8 mA V _{IS} = 0 V to 0.4 V	2.7 3.3 4.2	-	0.60 0.60 0.60	-	Ω

^{1.} Guaranteed by design.

FULL V_{IS} SWING ON RESISTANCE (Typical: T = 25°C)

					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
R _{ON}		On-Resistance	I _{ON} = 8 mA V _{IS} = 0 V to V _{CC}	2.7 3.3 4.2	-	10 8.0 7.0	13.5 9.75 8.50	Ω
R _{FLAT}		On-Resistance Flatness (Notes 4 and 5)	I _{ON} = 8 mA V _{IS} = 0 V to V _{CC}	2.7 3.3 4.2	-	4.5 3.0 2.5	-	Ω
ΔR_{ON}		On-Resistance (Note 4 and 6)	I _{ON} = 8 mA V _{IS} = 0 V to V _{CC}	2.7 3.3 4.2	-	0.60 0.60 0.60	-	Ω

^{2.} Flatness is defined as the difference between the maximum and minimum value of On-Resistance as measured over the specified analog

^{3.} $\Delta \ddot{R}_{ON} = \ddot{R}_{ON(max)} - R_{ON(min)}$ between HSD1+ and HSD1- or HSD2+ and HSD2-.

^{4.} Guaranteed by design.
5. Flatness is defined as the difference between the maximum and minimum value of On–Resistance as measured over the specified analog

^{6.} $\Delta R_{ON} = R_{ON(max)} - R_{ON(min)}$ between HSD1⁺ and HSD1⁻ or HSD2⁺ and HSD2⁻.

AC ELECTRICAL CHARACTERISTICS

TIMING/FREQUENCY (Typical: T = 25°C, V_{CC} = 3.3 V, R_L = 50 Ω , C_L = 35 pF, f = 1 MHz)

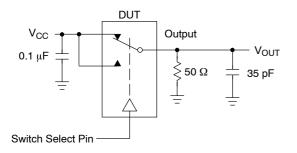
					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
t _{ON}	Closed to Open	Turn-ON Time (See Figures 4 and 5)		1.65 – 4.5	-	13.0	30.0	ns
t _{OFF}	Open to Closed	Turn-OFF Time (See Figures 4 and 5)		1.65 – 4.5	-	12.0	25.0	ns
T _{BBM}		Break-Before-Make Time (See Figure 3)		1.65 – 4.5	2.0	-	-	ns
BW		–3 dB Bandwidth (See Figure 10)	C _L = 5 pF	1.65 – 4.5	-	950	-	MHz

ISOLATION (Typical: T = 25°C, V_{CC} = 3.3 V, R_L = 50 Ω , C_L = 5 pF)

					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
O _{IRR}	Open	OFF-Isolation (See Figure 6)	f = 240 MHz	1.65 – 4.5	-	-22	-	dB
X _{TALK}	HSDn+ to HSDn-	Non-Adjacent Channel Crosstalk	f = 240 MHz	1.65 – 4.5	-	-24	-	dB

 $\textbf{CAPACITANCE} \text{ (Typical: } T = 25^{\circ}\text{C, V}_{CC} = 3.3 \text{ V, R}_{L} = 50 \text{ }\Omega\text{, C}_{L} = 5 \text{ pF)}$

				-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	Min	Тур	Max	Unit
C _{IN}	C _{IN} S, OE	Control Pin, Output Enable Input Capacitance	V _{CC} = 0 V, f = 1 MHz	_	1.5	_	pF
			V _{CC} = 0 V, f = 10 MHz	-	1.0	-	
C _{ON}	D+ to HSD1+ or HSD2+	ON Capacitance	V _{CC} = 3.3 V; OE = 0 V, f = 1 MHz S = 0 V or 3.3 V	-	7.5	-	
			V _{CC} = 3.3 V; OE = 0 V, f = 10 MHz S = 0 V or 3.3 V	-	6.5	-	
C _{OFF}	HSD1n or HSD2n		$\begin{tabular}{lll} $V_{CC} = V_{IS} = 3.3 \ V; \\ $\overline{OE} = 0 \ V, \ S = 3.3 \ V \ or \ 0 \ V, \\ $f = 1 \ MHz \end{tabular}$	-	3.8	-	
			$\begin{tabular}{lll} $V_{CC} = V_{IS} = 3.3 \ V; \\ $OE = 0 \ V, \ S = 3.3 \ V \ or \ 0 \ V, \\ $f = 10 \ MHz \end{tabular}$	-	2.0	-	



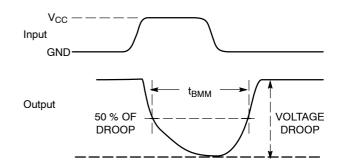
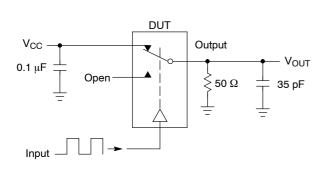


Figure 3. t_{BBM} (Time Break–Before–Make)



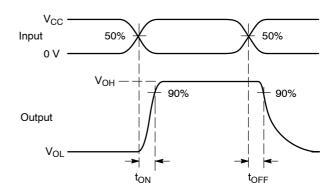
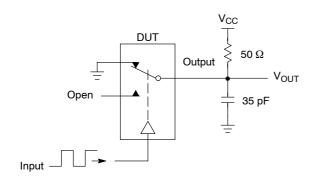


Figure 4. t_{ON}/t_{OFF}



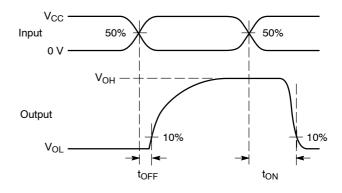
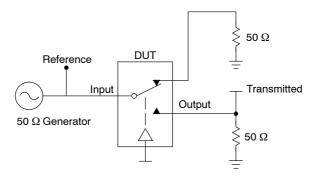


Figure 5. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$V_{ISO}$$
 = Off Channel Isolation = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz

 V_{ONL} = On Channel Loss = 20 Log $\left(\frac{V_{OUT}}{V_{IN}}\right)$ for V_{IN} at 100 kHz to 50 MHz

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

 V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

DETAILED DESCRIPTION

High Speed (480Mbps) USB 2.0 Optimized

The NLAS7242 is a DPDT switch designed for USB applications within portable systems. The R_{ON} and C_{ON} of both switches are maintained at industry–leading low levels in order to ensure maximum signal integrity for USB 2.0 high speed data communication. The NLAS7242 switch can be used to switch between high speed (480Mbps) USB signals and a variety of audio or data signals such as full speed USB, UART or even a moderately resistive audio terminal.

Over Voltage Tolerant

The NLAS7242 features over voltage tolerant I/O protection on the common signal pins D+/D-. This allows the switch to interface directly with a USB connector. The D+/D- pins can withstand a short to V_{BUS} , up to 5.25 V, continuous DC current for up to 24 hours as specified in the USB 2.0 specification. This protection is achieved without the need for any external resistors or protection devices.

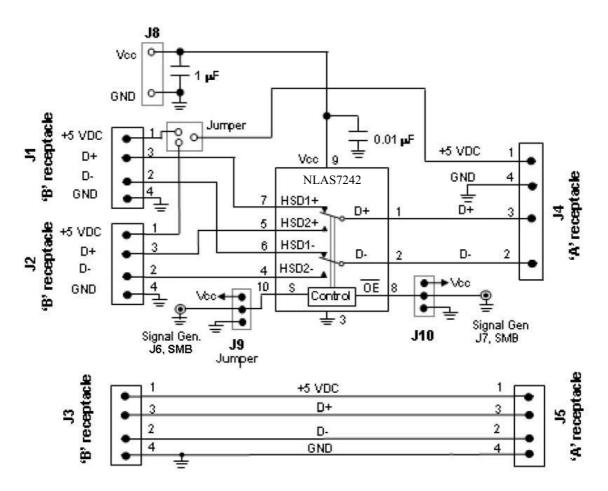


Figure 7. Board Schematic

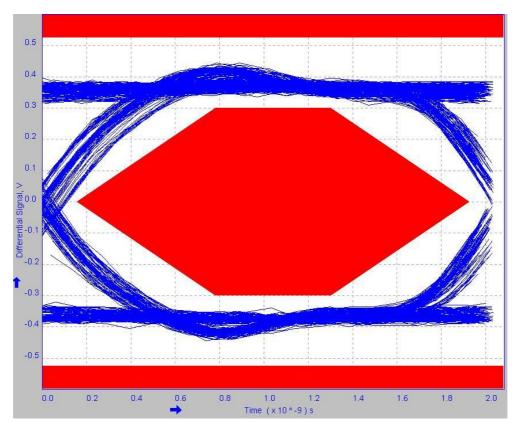


Figure 8. Signal Quality

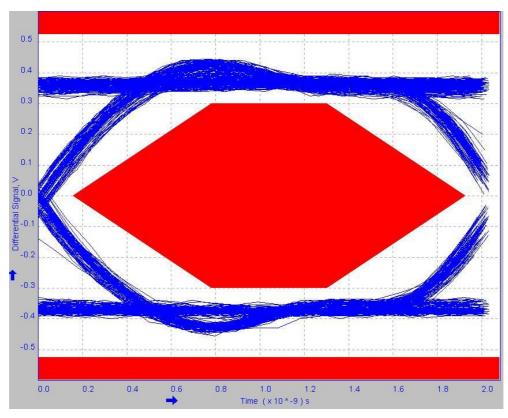


Figure 9. Near End Eye Diagram

Near End Test Data:					Min	Max
	Consecutive jitter range	-54.37	73.21	ps		+200 ps
Std.	Paired JK jitter range	-59.14	59.56	ps	–200 ps	
	Paired KJ jitter range	-50.79	34.57	ps		
	Consecutive jitter range	-74.43	81.65	ps		
N.C.	Paired JK jitter range	-61.60	58.55	ps	–200 ps	+200 ps
	Paired KJ jitter range	-55.31	48.43	ps]	
	Consecutive jitter range	-82.55	80.33	ps		
N.O.	Paired JK jitter range	-53.50	71.65	ps	-200 ps	+200 ps
	Paired KJ jitter range	-62.60	47.30	ps		

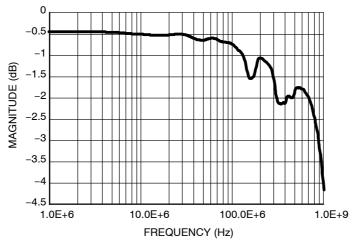


Figure 10. Magnitude vs. Frequency @ V_{CC} = 3.3 V, All Temperatures

I_{CC} Leakage Current as a Function of V_{IN} Voltage (25°C)

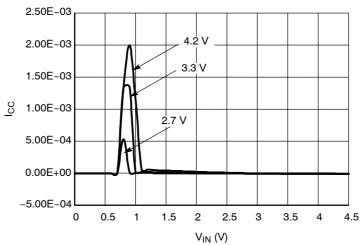
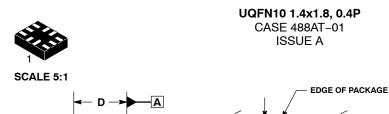


Figure 11. I_{CC} vs. V_{IN} , Select Pin, All V_{CC} 's, 25°C

PIN 1 REFERENCE

DATE 01 AUG 2007





- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM
- FROM TERMINAL.

 COPLANARITY APPLIES TO THE EXPOSED PAD
 AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.60		
A1	0.00 0.05			
A3	0.127 REF			
b	0.15	0.25		
D	1.40 BSC			
E	1.80 BSC			
е	0.40 BSC			
L	0.30	0.50		
L1	0.00	0.15		
L3	0.40	0.60		

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code М

= Pb-Free Package

(Note: Microdot may be in either location)

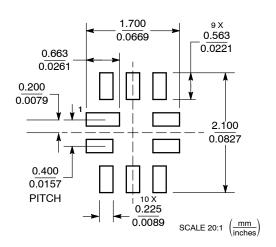
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DETAIL A 0.10 C **Bottom View** (Optional) 0.10 C MOLD CMPD EXPOSED Cu-В **TOP VIEW** АЗ 0.05 C 0.05 C \triangle **DETAIL B** Α1 SEATING PLANE Side View SIDE VIEW (Optional) 10 X 0.10 C A B

MOUNTING FOOTPRINT

BOTTOM VIEW

Œ 0.05 С



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DESCRIPTION:	10 PIN UQFN, 1.4 X 1.8, 0.4P		PAGE 1 OF 1	

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